

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.
209284US99SERIAL NO.
09/842,734

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Zhiyi YU, et al.

FILING DATE

April 26, 2001

GROUP

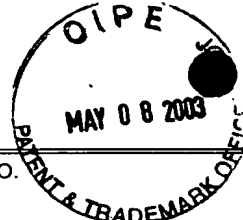
2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
SR	UT	5,528,209	06/18/96	Macdonald et al.			
	UV	5,998,781	12/07/99	Vawter et al.			
	UW	6,110,813	08/29/00	Ota et al.			
	UX	6,452,232 B1	09/17/02	Adan			
	UY	6,049,110	04/11/00	Koh			
	UZ	5,559,368	09/24/96	Hu et al.			
	VA	6,392,253 B1	05/21/02	Saxena			
	VB	5,585,288	12/17/96	Davis et al.			
	VC	5,268,327	12/07/93	Vernon			
	VD	6,198,119 B1	03/06/01	Nabatame et al.			
	VE	6,113,225	09/05/00	Miyata et al.			
	VF	5,262,659	11/16/93	Grudkowski et al.			
	VG	6,239,012 B1	05/29/01	Kinsman			
	VH	6,297,598	10/02/01	Wang et al.			
	VI	2002/140012	10/03/02	Droopad			
	VJ	4,866,489	09/12/89	Yokogawa et al.			
	VK	6,080,378	06/27/00	Yokota et al.			
	VL	5,508,554	04/16/96	Takatani et al.			
	VM	6,477,285 B1	11/05/02	Shanley			
	VN	4,695,120	09/22/87	Holder			
	VO	5,882,948	03/16/99	Jewell			
	VP	5,574,589	11/12/96	Feuer et al.			
	VQ	5,510,665	04/23/96	Conley			
	VR	4,804,866	02/14/89	Akiyama			
	VS	5,057,694	10/15/91	Idaka et al.			
	VT	5,635,453	06/03/97	Pique et al.			
	VU	5,719,417	02/17/98	Roeder et al.			
	VV	5,998,819	12/07/99	Yokoyama et al.			

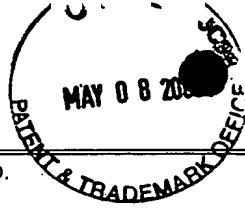
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TECHNOLOGY CENTER 2800Examiner *Shouyang Shu*Date Considered *11/04/03*

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<i>SPR</i> 	VW	2002/0079576	06/27/02	Seshan			
	VX	5,148,504	09/15/92	Levi et al.			
	VY	2002/0195610 A1	12/26/02	Klosowiak			
	VZ	5,477,363	12/19/95	Matsuda			
	WA	5,905,571	05/18/99	Butler et al.			
	WB	5,570,226	10/29/96	Ota			
	WC	5,087,829	02/11/92	Ishibashi et al.			
	WD	2001/0020278 A1	09/06/01	Saito			
	WE	6,496,469 B1	12/17/02	Uchizaki			
	WF	5,679,947	10/21/97	Doi et al.			
	WG	2001/0036142 A1	11/01/01	Kadowaki et al.			
	WH	5,446,719	08/29/95	Yoshida et al.			
	WI	5,831,960	11/03/98	Jiang et al.			
	WJ	5,693,140	12/02/97	McKee et al.			
	WK	6,376,337 B1	04/23/02	Wang et al.			
	WL	4,177,094	12/04/79	Kroon			
	WM	5,216,359	06/01/93	Makki et al.			
	WN	6,307,996 B1	10/23/01	Nashimoto et al.			
	WO	5,371,621	12/06/94	Stevens			
	WP	2002/0145168 A1	10/10/02	Bojarczuk, Jr et al.			
WQ	3,617,951	11/02/71	Anderson				
WR	5,838,053	11/17/98	Bevan et al.				
WS	5,684,302	11/04/97	Wersing et al.				
WT	5,959,308	09/28/99	Shichijo et al.				
WU	5,362,972	11/08/94	Yazawa et al.				
WV	5,864,171	01/26/99	Yamamoto et al.				
WW	5,028,563	07/02/91	Feit et al.				
WX	5,937,115	08/10/99	Domash				
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<i>Shouren</i>	WY	5,878,175	03/02/99	Sonoda et al.			
	WZ	4,801,184	01/31/89	Revelli			
	XA	5,140,387	08/18/92	Okazaki et al.			
	XB	5,410,622	04/25/95	Okada et al.			
	XC	6,064,783	05/16/00	Congdon et al.			
	XD	5,772,758	06/30/98	Collins et al.			
	XE	5,666,376	09/09/97	Cheng			
	XF	5,976,953	11/02/99	Zavracky et al.			
	XG	5,578,162	11/26/96	D'Asaro et al.			
	XH	5,585,167	12/17/96	Satoh et al.			
	XI	5,674,813	10/07/97	Nakamura et al.			
	XJ	5,574,296	11/12/96	Park et al.			
	XK	6,504,189	01/07/03	Matsuda et al.			
	XL	5,987,196	11/16/99	Noble			
	XM						
	XN						
XO							
XP							
XQ							
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XZ							
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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
<i>SPR</i>	CBC	EP 1 035 759	09/13/00	Europe		
	CBD	EP 0 860 913	08/26/95	EUROPE		
	CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT		
	CBF	5-243525	09/31/93	JAPAN W/ENGLISH ABSTRACT		
	CBG	3-171617	07/25/91	JAPAN W/ENGLISH ABSTRACT		
	CBH	EP 1 089 338	04/04/01	EUROPE		
	CBI	01 294594	11/28/99	JAPAN (ABSTRACT)		
	CBJ	05 221800	08/31/93	JAPAN (ABSTRACT)		
	CBK	03-149882	11/07/89	JAPAN		
	CBL	0 614 256	09/07/94	EUROPE		
	CBM	1 054 442	11/22/00	EUROPE		
	CBN	0 852 416	07/08/98	EUROPE		
	CBO	W0 02/08806	01/31/02	WIPO		
	CBP	W0 01/59837	08/16/01	WIPO		
	CBQ	62-245205	10/26/87	JAPAN W/ENGLISH ABSTRACT		
	CBR	0 600 658	06/08/94	EUROPE		
	CBS	0 412 002	02/06/91	EUROPE		
	CBT	2000-349278	12/15/00	JAPAN (ENGLISH ABSTRACT)		
	CBU	01-196809	08/08/89	JAPAN (ENGLISH ABSTRACT)		
	CBV	0 619 283	10/12/94	EUROPE		
	CBW	0 661 561	07/05/95	EUROPE		
	CBX	0 331 338	09/06/89	EUROPE		
	CBY					
	CBZ					
	CCA					
	CCB					
	CCC					
	CCD					
	CCE					
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>Sell</i>	KKAO	Charles Kittel; "Introduction to Solid State Physics"; John Wiley & Sons, Inc. Fifth Edition; pp. 415					
	KKAP	Chyuan-Wei Chen et al; "Liquid-phase epitaxial growth and characterization of InGaAsP layers grown on GaAsP substrates for application to orange light-emitting diodes"; 931 Journal of Applied Physics; 77 (1995) 15 January, No. 2; Woodbury, NY, US; pp. 905-909					
	KKAQ	W. Zhu et al.; "Oriented diamond films grown on nickel substrates"; 320 Applied Physics Letters; 63(1993) September, No. 12, Woodbury, NY, US; pp. 1640-1642					
	KKAR	M. Schreck et al.; "Diamond/Ir/SrTiO3: A material combination for improved heteroepitaxial diamond films"; Applied Physics Letters; Vol. 74, No. 5; February 1, 1999; pp. 650-652					
	KKAS	Yoshihiro Yokota et al.; "Cathodoluminescence of boron-doped heteroepitaxial diamond films on platinum"; Diamond and Related Materials 8(1999); pp. 1587-1591					
	KKAT	J.R. Busch et al.; "LINEAR ELECTRO-OPTIC RESPONSE IN SOL-GEL PZT PLANAR WAVEGUIDE"; Electronics Letters; 13th August 1992; Vol. 28, No. 17; pp. 1591-1592					
	KKAU	R. Droopad et al; "Epitaxial Oxide Films on Silicon: Growth, Modeling and Device Properties"; Mat. Res. Soc. Symp. Proc. Vol. 619; 2000 Materials Research Society; pp. 155-165					
	KKAV	H. Ohkubo et al.; "Fabrication of High Quality Perovskite Oxide Films by Lateral Epitaxy Verified with RHEED Oscillation"; 2419A Int. Conf. on Solid State Devices & Materials, Tsukuba, August 26-28 (1992); pp. 457-459					
	KKAW	Lin Li; "Ferroelectric/Superconductor Heterostructures"; Materials Science and Engineering; 29 (2000) pp. 153-181					
	KKAX	L. Fan et al.; "Dynaamic Beam Switching of Vertical-Cavity Surface-Emitting Lasers with Integrated Optical Beam Routers"; IEEE Photonics Technology Letters; Vol. 9, No. 4; April 4, 1997; pp. 505-507					
	KKAY	Y. Q. Xu. et al.; "(Mn, Sb) dropped-Pb(Zr,Ti)O3 infrared detector arrays"; Journal of Applied Physics; Vol. 88, No. 2; 15 July 2000; pp. 1004-1007					
	KKAZ	Kiyoko Kato et al.; "Reduction of dislocations in InGaAs layer on GaAs using epitaxial lateral overgrowth"; 2300 Journal of Crystal Growth 115 (1991) pp. 174-179; December 1991					
	LLAA						
	LLAB						
	LLAC						
	LLAD						
	LLAE						
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